

SN74AHCT1G32-Q1 車載対応、シングル 2 入力、正論理 OR ゲート

1 特長

- 車載アプリケーション向け認定済み
- 動作範囲: 4.5V~5.5V
- 最大 t_{pd} 9.5ns (5V 時)
- 低消費電力、最大 I_{CC} : 20 μ A
- 出力駆動能力: ± 8 mA (5V 時)
- 入力は TTL 電圧互換

2 アプリケーション

- デジタル信号のイネーブルまたはディセーブル
- インジケータ LED の制御
- 通信モジュールとシステム・コントローラの間の変換

3 概要

SN74AHCT1G32-Q1 はシングル 2 入力正論理 OR ゲートです。このデバイスはブール関数 $Y = A + B$ 、つまり $Y = \overline{A} \times \overline{B}$ を正論理で実行します。

パッケージ情報

部品番号	パッケージ ⁽¹⁾	パッケージサイズ ⁽²⁾	本体サイズ ⁽³⁾
SN74AHCT1G32-Q1	DBV (SOT-23, 5)	2.9mm × 2.8mm	2.9mm × 1.6mm
	DCK (SC-70, 5)	2.00mm × 1.25mm	2.00mm × 1.25mm

- 利用可能なすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。
- パッケージサイズ (長さ×幅) は公称値で、該当する場合はピンも含まれます。
- 本体サイズ (長さ×幅) は公称値であり、ピンは含まれません。



論理図 (正論理)

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4 Pin Configuration and Functions

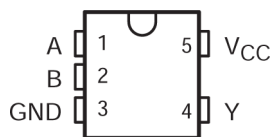


図 4-1. DBV or DCK Package, SOT-23 or SC70 5-Pin (Top View)

表 4-1. Pin Functions

PIN		TYPE ¹	DESCRIPTION
NAME	NO.		
A	1	I	Input A
B	2	I	Input B
GND	3	—	Ground Pin
Y	4	O	Output Y
V _{CC}	5	—	Power Pin

1. I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	−0.5	7	V
V _I	Input voltage	−0.5	7	V
V _O	Output voltage	−0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		−20 mA
I _{OK}	Output clamp current	V _O < 0 or V _O > V _{CC}		±20 mA
I _O	Continuous output current	V _O = 0 to V _{CC}		±25 mA
	Continuous current through V _{CC} or GND			±50 mA
T _{stg}	Storage temperature range	−65	150	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

Note: The input and output voltage ratings may be exceeded if the input and output current ratings are observed. The package thermal impedance is calculated in accordance with JESD 51-7.

5.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾	±2000
		Charged-Device Model (C5), per AEC Q100-011, all pins	±1000

- (1) AEC Q100-002 indicates that HBM stressing must be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	4.5	5.5	V
V _{IH}	High-level input voltage	2		V
V _{IL}	Low-level input voltage		0.8	V
V _I	Input voltage	0	5.5	V
V _O	Output voltage	0	V _{CC}	V
I _{OH}	High-level output current		−8	mA
I _{OL}	Low-level output current		8	mA
Δt/Δv	Input transition rise or fall rate		20	ns/V
T _A	Operating free-air temperature	−40	125	°C

- (1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs* (SCBA004).

5.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74AHCT1G32-Q1		UNIT
		DBV (SOT-23)	DCK (SC-70)	
		5 PINS	5 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	278	289.2	°C/W

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report (SPRA953).

5.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	T _A = 25°C			–40°C to 85°C		–40°C to 125°C		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V _{OH} High level output voltage	I _{OH} = –50 µA I _{OH} = –8 mA	4.5 V	4.4	4.5		4.4		4.4		V
V _{OL} Low level output voltage	I _{OL} = 50 µA I _{OL} = 8 mA	4.5 V			0.1 0.36		0.1 0.44		0.1 0.52	V
I _I Input leakage current	V _I = 5.5 V or GND	0 V to 5.5 V			±0.1		±1		±1	µA
I _{CC} Supply current	V _I = V _{CC} or GND, I _O = 0	5.5 V			1		10		20	µA
ΔI _{CC} ⁽¹⁾ Supply-current change	One input at 3.4 V, Other inputs at V _{CC} or GND	5.5 V			1.35		1.5		1.65	mA
C _i Input Capacitance	V _I = V _{CC} or GND	5 V		2	10		10		10	pF

(1) This is the increase in supply current for each input at one of the specified TTL voltage levels, rather than 0 V or V_{CC}.

5.6 Switching Characteristics

over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see [Load Circuit and Voltage Waveforms](#))

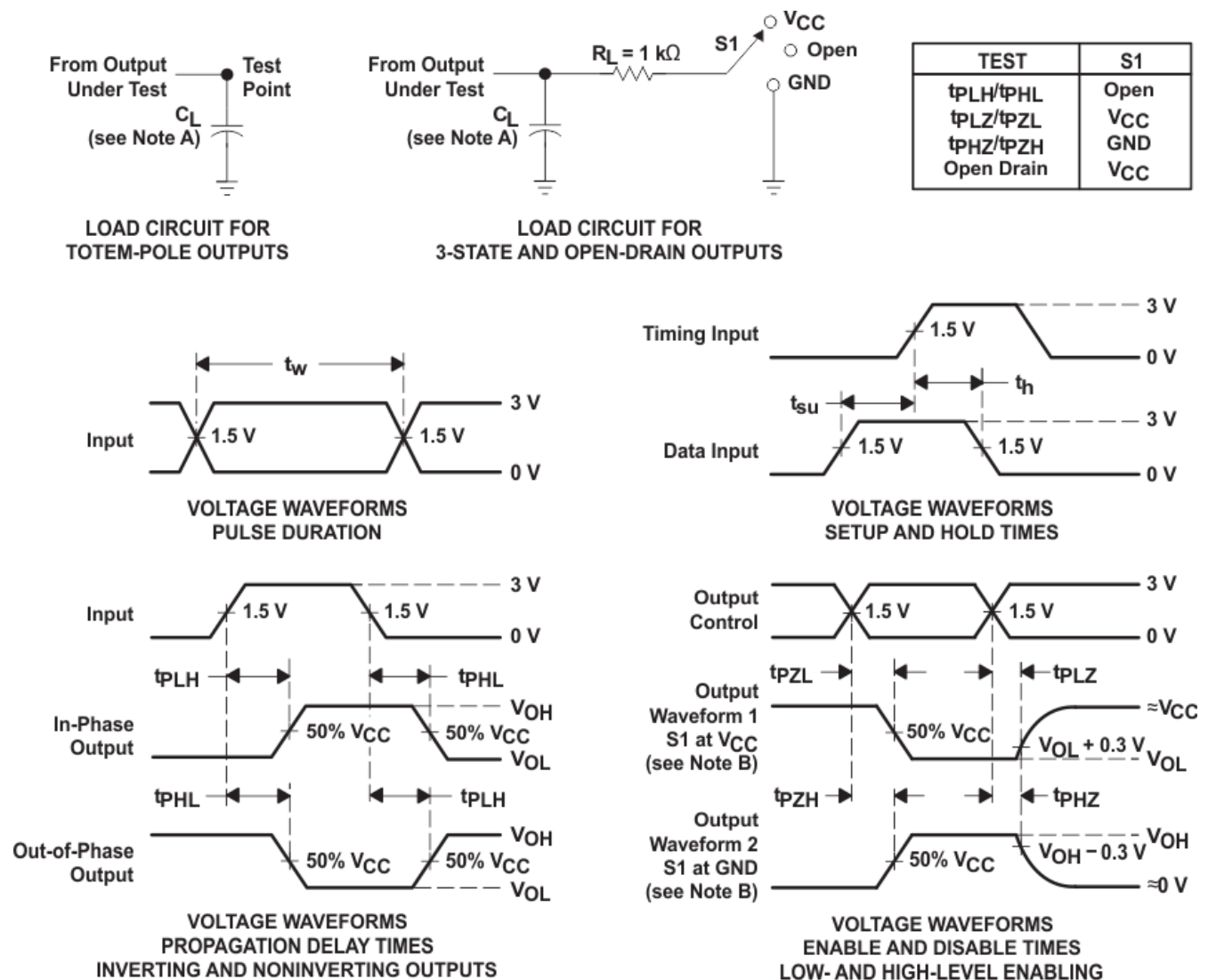
PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T _A = 25°C			–40°C to 85°C		–40°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t _{PLH}	A or B	Y	C _L = 15 pF		5	6.9	1	8		9.5	ns
t _{PHL}					5	6.9	1	8		9.5	
t _{PLH}	A or B	Y	C _L = 50 pF		5.5	7.9	1	9		10.5	ns
t _{PHL}					5.5	7.9	1	9		10.5	

5.7 Operating Characteristics

V_{CC} = 5 V, T_A = 25°C

PARAMETER	TEST CONDITIONS	TYP	UNIT
C _{pd} Power dissipation capacitance	No load, f = 1 MHz	11.5	pF

6 Parameter Measurement Information



- NOTES: A. C_L includes probe and jig capacitance.
 B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 3\text{ ns}$, $t_f \leq 3\text{ ns}$.
 D. The outputs are measured one at a time, with one input transition per measurement.
 E. All parameters and waveforms are not applicable to all devices.

图 6-1. Load Circuit and Voltage Waveforms

7 Detailed Description

7.1 Overview

The SN74AHCT1G32-Q1 device is a single 2-input positive-OR gate. The device performs the Boolean function $Y = A + B$ or $Y = \overline{A \times B}$ in positive logic.

The device has TTL inputs that allow up translation from 3.3 V to 5 V. The inputs are high impedance when $V_{CC} = 0$ V.

7.2 Functional Block Diagram



図 7-1. Logic Diagram (Positive Logic)

7.3 Feature Description

- Slow rise and fall time on outputs allow for low noise outputs.
- TTL inputs Allows up translation from 3.3 V to 5 V

7.4 Device Functional Modes

表 7-1. Function Table

INPUTS ⁽¹⁾		OUTPUT ⁽²⁾
A	B	Y
H	X	H
X	H	H
L	L	L

- (1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care
- (2) H = Driving High, L = Driving Low, Z = High Impedance State

8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Typical Application

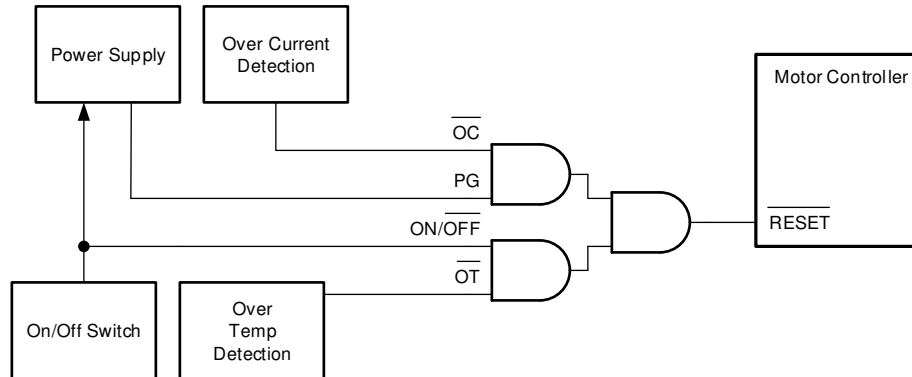


図 8-1. Typical Application Block Diagram

8.1.1 Design Requirements

8.1.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the electrical characteristics of the device as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74AHCT1G32-Q1 plus the maximum static supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74AHCT1G32-Q1 plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74AHCT1G32-Q1 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74AHCT1G32-Q1 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in the [CMOS Power Consumption and Cpd Calculation](#) application note.

Thermal increase can be calculated using the information provided in the [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#) application note.

注意

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

8.1.1.2 Input Considerations

Input signals must cross $V_{IL(max)}$ $V_{t(min)}$ to be considered a logic LOW, and $V_{IH(min)}$ $V_{t+(max)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74AHCT1G32-Q1 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k Ω resistor value is often used due to these factors.

The SN74AHCT1G32-Q1 has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

The SN74AHCT1G32-Q1 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the $\Delta V_{T(min)}$ in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

8.1.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Open-drain outputs can be connected together directly to produce a wired-AND configuration or for additional output drive strength.

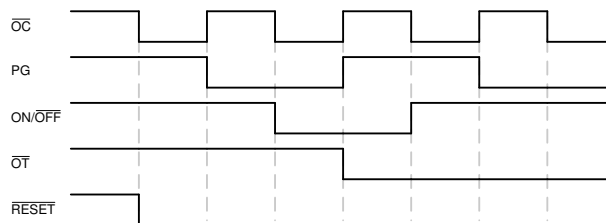
Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

8.1.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; it will, however, ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74AHCT1G32-Q1 to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$, so that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in $M\Omega$; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

8.1.3 Application Curves



8-2. Application Timing Diagram

8.2 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the [セクション 5.3](#) table.

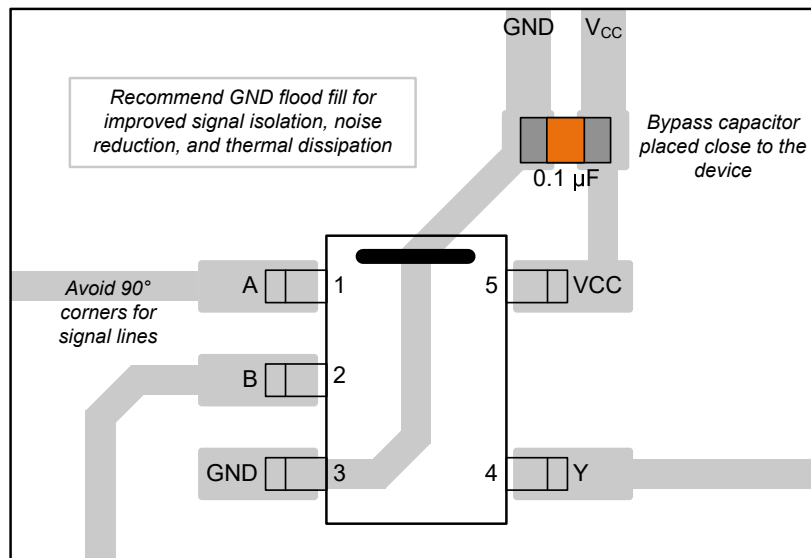
Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 μF is recommended. If there are multiple V_{CC} pins, 0.01 μF or 0.022 μF is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1 μF and 1 μF are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

8.3 Layout

8.3.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices, inputs must never be left floating. In many cases, functions or parts of functions of digital logic devices are unused (for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used). Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

8.3.1.1 Layout Example



✎ 8-3. Example Layout for the SN74AHCT1G32-Q1

9 Device and Documentation Support

9.1 Documentation Support (Analog)

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and Cpd Calculation application note](#)
- Texas Instruments, [Designing With Logic application note](#)
- Texas Instruments, [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices application note](#)
- Texas Instruments, [Implications of Slow or Floating CMOS Inputs application note](#)

9.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

9.3 サポート・リソース

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9.4 Trademarks

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9.5 静電気放電に関する注意事項



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ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

9.6 用語集

テキサス・インスツルメンツ用語集

この用語集には、用語や略語の一覧および定義が記載されています。

10 Revision History

Changes from Revision D (October 2023) to Revision E (February 2024)

	Page
• 「パッケージ情報」表に本体サイズを追加	1
• Updated RθJA value: DBV = 206 to 278, all values in °C/W	4

Changes from Revision C (November 2022) to Revision D (October 2023)

	Page
• 「アプリケーション」セクションを追加、タイトルを更新、「パッケージ情報」表、「ピン機能」表にパッケージサイズを追加、「アプリケーションと実装」セクションを追加、「熱に関する情報」表を追加、「関連資料」を追加	1
• Removed machine model from <i>ESD Ratings</i> table.....	4
• Updated RθJA values: DCK = 252 to 289.2, all values in °C/W	4

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CAHCT1G32QDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	B32U	Samples
CAHCT1G32QDCKRQ1	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	BGU	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74AHCT1G32-Q1 :

- Catalog : [SN74AHCT1G32](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CAHCT1G32QDBVRQ1	SOT-23	DBV	5	3000	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
CAHCT1G32QDCKRQ1	SC70	DCK	5	3000	179.0	8.4	2.2	2.5	1.2	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

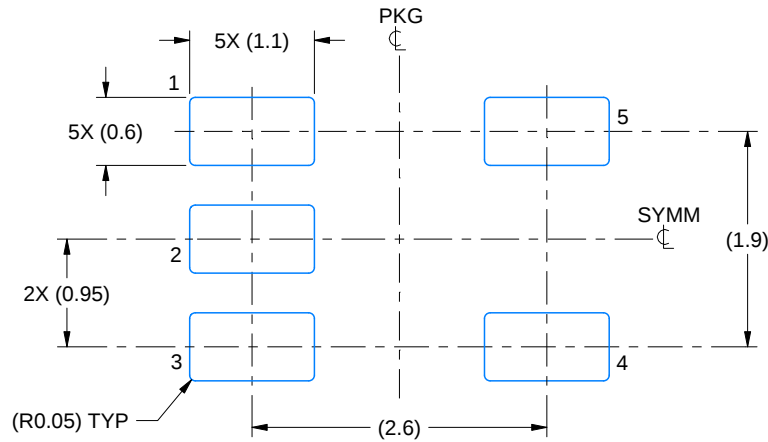
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CAHCT1G32QDBVRQ1	SOT-23	DBV	5	3000	200.0	183.0	25.0
CAHCT1G32QDCKRQ1	SC70	DCK	5	3000	200.0	183.0	25.0

EXAMPLE BOARD LAYOUT

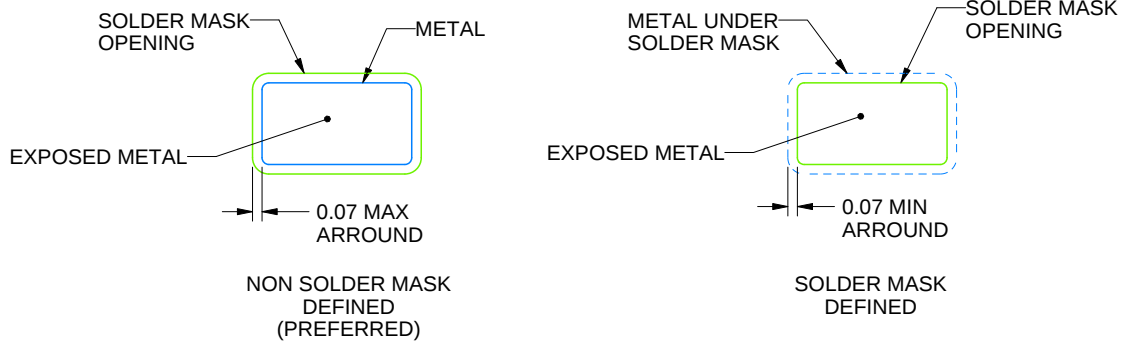
DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214839/J 02/2024

NOTES: (continued)

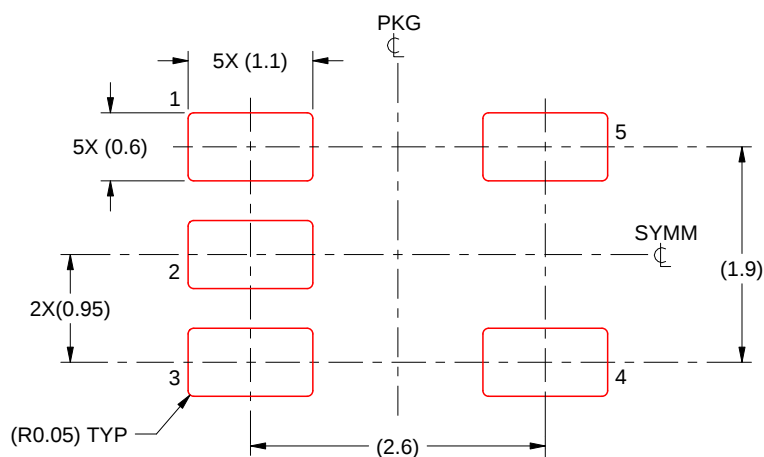
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR

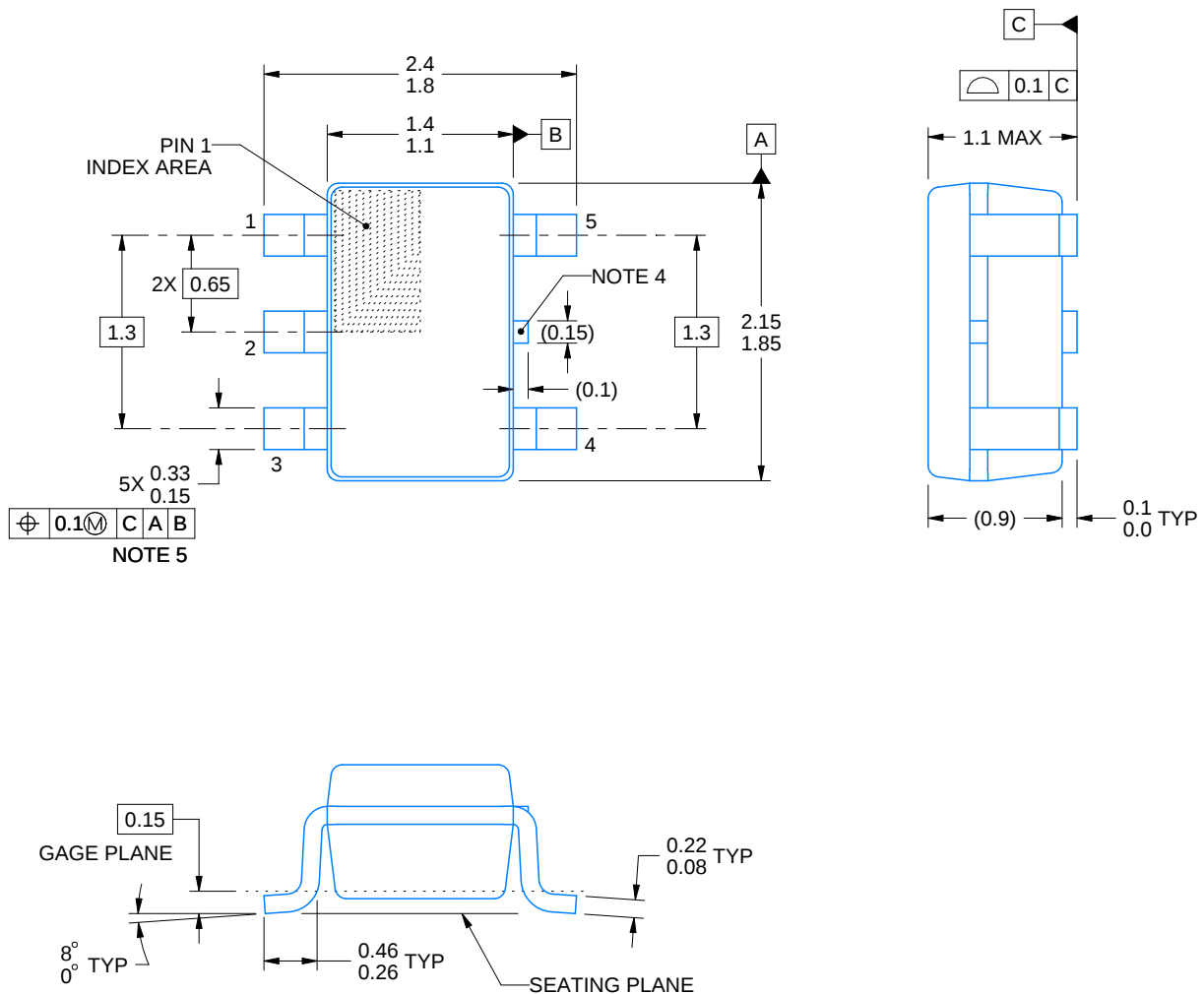


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



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NOTES:

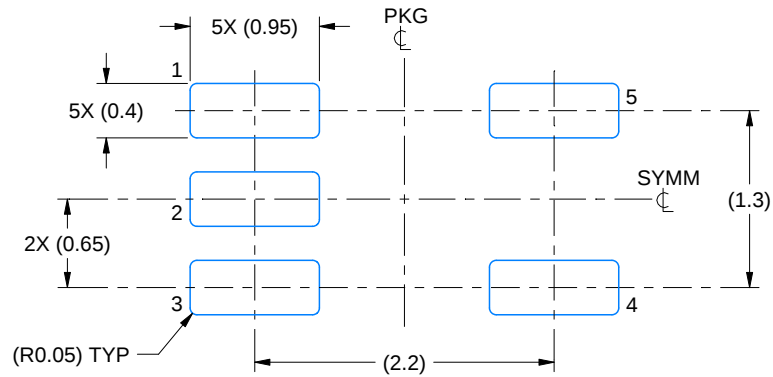
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.

EXAMPLE BOARD LAYOUT

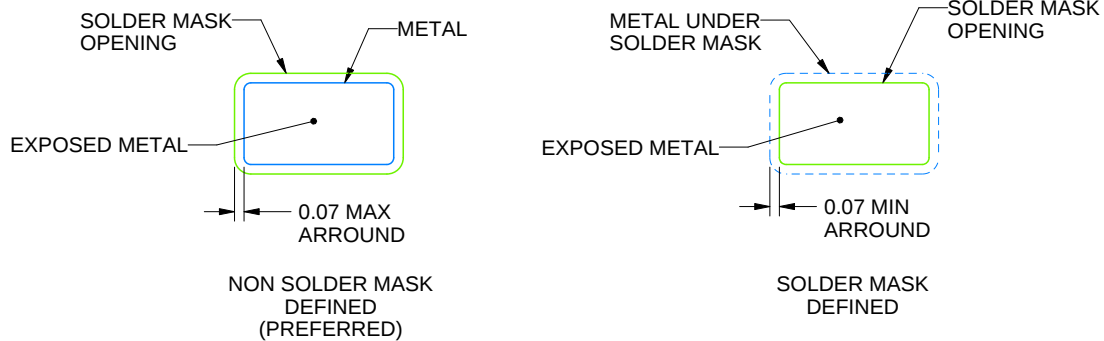
DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X

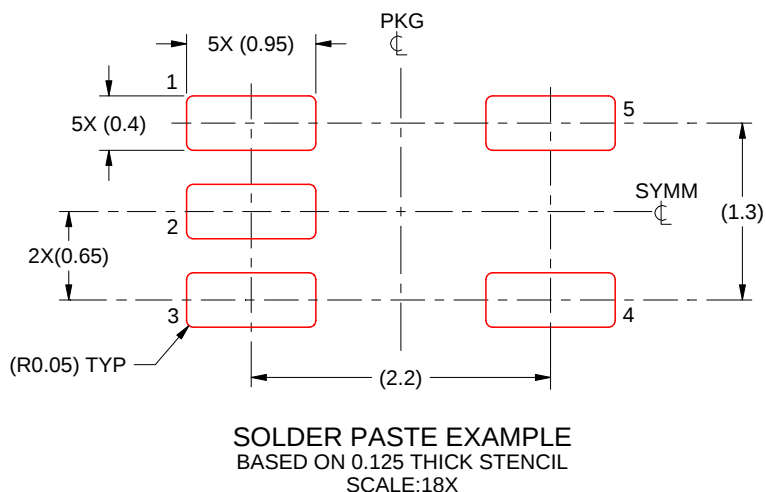


SOLDER MASK DETAILS

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NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



4214834/D 07/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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